

ZTX457STZ Datasheet



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DiGi Electronics Part Number ZTX457STZ-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number ZTX457STZ

Description TRANS NPN 300V 0.5A E-LINE

Detailed Description Bipolar (BJT) Transistor NPN 300 V 500 mA 75MHz 1

W Through Hole E-Line (TO-92 compatible)



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:	
ZTX457STZ	Diodes Incorporated	
Series:	Product Status:	
	Active	
Transistor Type:	Current - Collector (Ic) (Max):	
NPN	500 mA	
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:	
300 V	300mV @ 10mA, 100mA	
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:	
100nA (ICBO)	50 @ 50mA, 10V	
Power - Max:	Frequency - Transition:	
1 W	75MHz	
Operating Temperature:	Mounting Type:	
-55°C ~ 200°C (TJ)	Through Hole	
Package / Case:	Supplier Device Package:	
E-Line-3, Formed Leads	E-Line (TO-92 compatible)	
Base Product Number:		
717/157		

Environmental & Export classification

8541.29.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

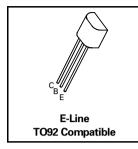
NPN SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

ZTX457

ISSUE 2 – MARCH 1994

FEATURES

- * 300 Volt V_{CEO}
- * 0.5 Amp continuous current
- * P_{tot}= 1 Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I _{CM}	1	Α
Continuous Collector Current	I _C	500	mA
Power Dissipation at T _{amb} =25°C	P _{tot}	1	W
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

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PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	300			V	$I_{C}=100\mu A, I_{E}=0$
Collector-Emitter Breakdown Voltage	V _{CEO(sus)}	300			V	I _C =10mA, I _B =0*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5			V	I _E =100μA
Collector Cut-Off Current	I _{CBO}			100 10	nA μA	V _{CB} =200V V _{CB} =200V, T _{amb} =100°C
Emitter Cut-Off Current	I _{EBO}			100	nA	V _{EB} =4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.3	V	I _C =100mA, I _B =10mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			1	V	I _C =100mA, I _B =10mA*
Base-Emitter Turn On Voltage	V _{BE(on)}			1	V	IC=100mA, V _{CE} =10V*
Static Forward Current Transfer Ratio	h _{FE}	50 50 25		300		I _C =10mA, V _{CE} =10V* I _C =50mA, V _{CE} =10V* I _C =100mA, V _{CE} =10V*
Transition Frequency	f _T	75			MHz	I _C =50mA, V _{CE} =10V f=20MHz

^{*}Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle \leq 2%



OUR CERTIFICATE

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